

Silicon NPN Power Transistors

2SC2767

DESCRIPTION

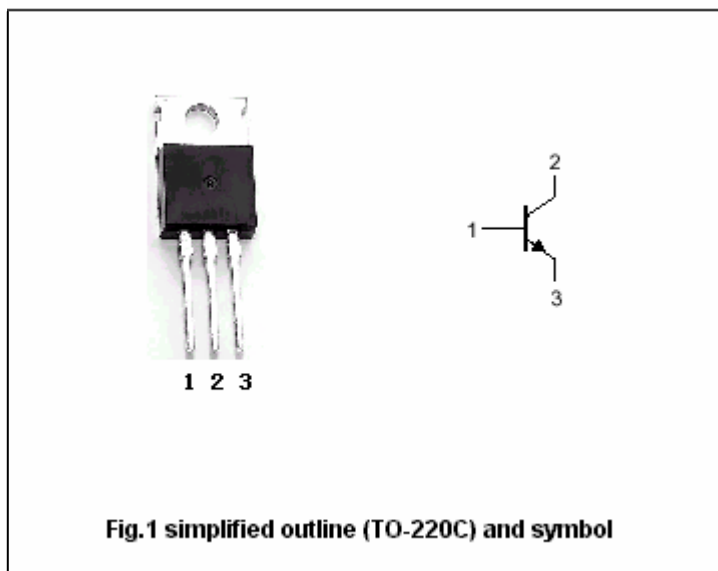
- With TO-220C package
- High speed switching
- High reliability

APPLICATIONS

- Switching regulators
- Ultrasonic generators
- High frequency inverters
- General purpose power amplifiers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings($T_a=25^\circ\text{C}$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	250	V
V_{CEO}	Collector-emitter voltage	Open base	200	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		5	A
I_B	Base current		1.5	A
P_C	Collector power dissipation	$T_C=25^\circ\text{C}$	40	W
T_j	Junction temperature		150	$^\circ\text{C}$
T_{stg}	Storage temperature		-55~150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th\ j-C}$	Thermal resistance junction case	3.0	$^\circ\text{C}/\text{W}$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	$I_C=25mA$; $I_B=0$	200			V
$V_{(BR)CBO}$	Collector-base breakdown voltage	$I_C=100\mu A$; $I_E=0$	250			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=100\mu A$; $I_C=0$	7			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=2A$; $I_B=0.8A$			0.2	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=2A$; $I_B=0.8A$			1.0	V
I_{CBO}	Collector cut-off current	$V_{CB}=250V$; $I_E=0$			10	μA
I_{EBO}	Emitter cut-off current	$V_{EB}=7V$; $I_C=0$			100	μA
h_{FE}	DC current gain	$I_C=1A$; $V_{CE}=5V$	20		80	

Switching times

t_{on}	Turn-on time	$I_C=4A$; $I_{B1}=-I_{B2}=-0.4A$ $R_L=20\Omega$			1.0	μs
t_{stg}	Storage time				2.0	μs
t_f	Fall time				1.0	μs

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PACKAGE OUTLINE

Fig.2 Outline dimensions (unindicated tolerance: ± 0.10 mm)

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